



Description

RoHS **Compliant**

MLCC consists of a conducting material and electrodes. To manufacture a chip-type SMT and achieve miniaturization, high density and high efficiency, ceramic condensers are used. This RF series MLCC is used at high frequencies generally have a small temperature coefficient of capacitance, typical within the ±30ppm/°C required for NP0 (C0G) & X8G classification and have excellent conductivity internal electrode. Thus, This RF series MLCC will be with the feature of low ESR and high Q characteristics.

Features

- High Q and low ESR performance at high frequency.
- Ultra low capacitance to 0.1pF.
- Can offer high precision tolerance to ±0.05pF.
- Quality improvement of telephone calls for low power loss and better performance

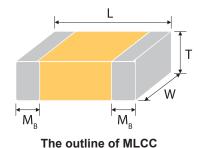
Applications

- Telecommunication products & equipments: Mobile phone, WLAN, Base station.
- RF module: Power amplifier, VCO.
- Tuners.

External Dimensions:

Size Inch (mm)	L (mm)	W (mm)	T (mm)/Symbol		Remark	Mв min (mm)
0402 (1005)	1±0.05	0.5±0.05	0.5±0.05	N	#	0.25+0.05/-0.1

[#] Reflow soldering only is recommended.



General Electrical Data:

Dielectric	NP0
Size	0402 (1005)
Capacitance*	0.1pF to 1000pF
Capacitance tolerance	Cap<10pF: A (±0.05pF), B (±0.1pF), C (±0.25pF), D (±0.5pF) Cap≥10pF: F (±1%), G (±2%), J (±5%)
Rated voltage (WVDC)	6.3V, 10V, 25V, 50V, 100V, 200V, 250V, 500V, 1500V
Q*	01005, 0201, 0402/25V~50V: Cap<30pF:Q≥400+20C; Cap≥30pF:Q≥1000 0402/100V~200V, 0603, 0805, 0505, 1111: Cap<30pF:Q≥800+20C; Cap≥30pF:Q≥1400
Insulation resistance at Ur	≥10GΩ or RxC≥100Ω-F whichever is smaller.
Operating temperature	-55°C to +125°C
Capacitance change	±30ppm/°C
Termination	Ni/Sn (lead-free termination)

^{*} Measured at 1 ±0.2Vrms, 1MHz ±10% for Cap≤1,000pF and 1 ±0.2Vrms, 1kHz ±10% for Cap>1,000pF, 25°C at ambient temperature for NP0.



^{*}Measured at 1.0±0.2Vrms, 1.0kHz±10% for C≤10µF; 0.5±0.2Vrms, 120Hz±20% for C>10µF, 30~70% related humidity, 25°C ambient temperature for X7R.

^{**} Preconditioning for Class II MLCC: Perform a heat treatment at 150 ±10°C for 1 hour, then leave in ambient condition for 24±2 hours before measurement.



Capacitance Range (NP0)

Dielectric				NP0		
Size			0402		Talamana	
Rated	Voltage (V DC)	25	50	100	200	Tolerance
	0.1pF (0R1)	N	N	N	N	A, B
	0.2pF (0R2)	N	N	N	N	A, B
	0.3pF (0R3)	N	N	N	N	A, B
	0.4pF (0R4)	N	N	N	N	A, B
	0.5pF (0R5)	N	N	N	N	A, B, C
	0.6pF (0R6)	N	N	N	N	A, B, C
	0.7pF (0R7)	N	N	N	N	A, B, C
	0.75pF (R75)	N	N	N	N	A, B, C
	0.8pF (0R8)	N	N	N	N	A, B, C
	0.9pF (0R9)	N	N	N	N	A, B, C
	1.0pF (1R0)	N	N	N	N	A, B, C
	1.1pF (1R1)	N	N	N	N	A, B, C
	1.2pF (1R2)	N	N	N	N	A, B, C
	1.3pF (1R3)	N	N	N	N	A, B, C
4)	1.4pF (1R4)	N	N	N	N	A, B, C
ance	1.5pF (1R5)	N	N	N	N	A, B, C
acita	1.6pF (1R6)	N	N	N	N	A, B, C
Capacitance	1.8pF (1R8)	N	N	N	N	A, B, C
O	2.0pF (2R0)	N	N	N	N	A, B, C
	2.2pF (2R2)	N	N	N	N	A, B, C
	2.4pF (2R4)	N	N	N	N	A, B, C
	2.5pF (2R5)	N	N	N	N	A, B, C
	2.6pF (2R6)	N	N	N	N	A, B, C
	2.7pF (2R7)	N	N	N	N	A, B, C
	2.8pF (2R8)	N	N	N	N	A, B, C
	2.9pF (2R9)	N	N	N	N	A, B, C
	3.0pF (3R0)	N	N	N	N	A, B, C
	3.1pF (3R1)	N	N	N	N	A, B, C
	3.2pF (3R2)	N	N	N	N	A, B, C
	3.3pF (3R3)	N	N	N	N	A, B, C
	3.4pF (3R4)	N	N	N	N	A, B, C
	3.5pF (3R5)	N	N	N	N	A, B, C
	3.6pF (3R6)	N	N	N	N	A, B, C
	3.7pF (3R7)	N	N	N	N	A, B, C

^{1.} The letter in cell is expressed the symbol of product thickness.





Dielectric				NP0		
	Size	0402				
Rated	Voltage (V DC)	25	50	100	200	Tolerance
	3.8pF (3R8)	N	N	N	N	A, B, C
	3.9pF (3R9)	N	N	N	N	A, B, C
	4.0pF (4R0)	N	N	N	N	A, B, C
	4.1pF (4R1)	N	N	N	N	A, B, C
	4.2pF (4R2)	N	N	N	N	A, B, C
	4.3pF (4R3)	N	N	N	N	A, B, C
	4.4pF (4R4)	N	N	N	N	A, B, C
	4.5pF (4R5)	Ν	N	N	N	A, B, C
	4.6pF (4R6)	N	N	N	N	A, B, C
	4.7pF (4R7)	N	N	N	N	A, B, C
	4.8pF (4R8)	N	N	N	N	A, B, C
	4.9pF (4R9)	N	N	N	N	A, B, C
	5.0pF (5R0)	N	N	N	N	A, B, C
	5.1pF (5R1)	Ν	N	N	N	A, B, C, D
	5.2pF (5R2)	N	N	N	N	A, B, C, D
ge	5.3pF (5R3)	N	N	N	N	A, B, C, D
Capacitance	5.4pF (5R4)	N	N	N	N	A, B, C, D
pac	5.5pF (5R5)	N	N	N	N	A, B, C, D
ပိ	5.6pF (5R6)	N	N	N	N	A, B, C, D
	5.7pF (5R7)	N	N	N	N	A, B, C, D
	5.8pF (5R8)	N	N	N	N	A, B, C, D
	5.9pF (5R9)	N	N	N	N	A, B, C, D
	6.0pF (6R0)	N	N	N	N	A, B, C, D
	6.1pF (6R1)	N	N	N	N	A, B, C, D
	6.2pF (6R2)	N	N	N	N	A, B, C, D
	6.3pF (6R3)	N	N	N	N	A, B, C, D
	6.4pF (6R4)	N	N	N	N	A, B, C, D
	6.5pF (6R5)	N	N	N	N	A, B, C, D
	6.6pF (6R6)	N	N	N	N	A, B, C, D
	6.7pF (6R7)	N	N	N	N	A, B, C, D
	6.8pF (6R8)	N	N	N	N	A, B, C, D
	6.9pF (6R9)	N	N	N	N	A, B, C, D
	7.0pF (7R0)	N	N	N	N	A, B, C, D
	7.1pF (7R1)	N	N	N	N	A, B, C, D

^{1.} The letter in cell is expressed the symbol of product thickness.



ı	Dielectric			NP0		
Size			0402			
Rated	Voltage (V DC)	25	50	100	200	Tolerance
	7.2pF (7R2)	N	N	N	N	A, B, C, D
	7.3pF (7R3)	N	N	N	N	A, B, C, D
	7.4pF (7R4)	N	N	N	N	A, B, C, D
	7.5pF (7R5)	N	N	N	N	A, B, C, D
	7.6pF (7R6)	N	N	N	N	A, B, C, D
	7.7pF (7R7)	N	N	N	N	A, B, C, D
	7.8pF (7R8)	N	N	N	N	A, B, C, D
	7.9pF (7R9)	N	N	N	N	A, B, C, D
	8.0pF (8R0)	N	N	N	N	A, B, C, D
	8.1pF (8R1)	N	N	N	N	A, B, C, D
	8.2pF (8R2)	N	N	N	N	A, B, C, D
	8.3pF (8R3)	N	N	N	N	A, B, C, D
	8.4pF (8R4)	N	N	N	N	A, B, C, D
	8.5pF (8R5)	N	N	N	N	A, B, C, D
	8.6pF (8R6)	N	N	N	N	A, B, C, D
	8.7pF (8R7)	N	N	N	N	A, B, C, D
Capacitance	8.8pF (8R8)	N	N	N	N	A, B, C, D
acita	8.9pF (8R9)	N	N	N	N	A, B, C, D
Sap	9.0pF (9R0)	N	N	N	N	A, B, C, D
	9.1pF (9R1)	N	N	N	N	A, B, C, D
	9.2pF (9R2)	N	N	N	N	A, B, C, D
	9.3pF (9R3)	N	N	N	N	A, B, C, D
	9.4pF (9R4)	N	N	N	N	A, B, C, D
	9.5pF (9R5)	N	N	N	N	A, B, C, D
	9.6pF (9R6)	N	N	N	N	A, B, C, D
	9.7pF (9R7)	N	N	N	N	A, B, C, D
	9.8pF (9R8)	N	N	N	N	A, B, C, D
	9.9pF (9R9)	N	N	N	N	A, B, C, D
	10pF (100)	N	N	N	N	F,G, J
	11pF (110	N	N	N	N	F,G, J
	12pF (120)	N	N	N	N	F,G, J
	13pF (130)	N	N	N	N	F,G, J
	15pF (150)	N	N	N	N	F,G, J
	16pF (160)	N	N	N	N	F,G, J
	18pF (180)	N	N	N	N	F,G, J

^{1.} The letter in cell is expressed the symbol of product thickness.



	Dielectric		NP0					
	Size	0402				Toloronoo		
Rated '	Voltage (V DC)	25	50	100	200	- Tolerance		
	20pF (200)	N	N	N	N	F,G, J		
	22pF (220)	N	N	N	N	F,G, J		
	24pF (240)	N	N	N	N	F,G, J		
	27pF (270)	N	N	N	N	F,G, J		
	30pF (300)	N	N	N	N	F,G, J		
99	33pF (330)	N	N	N	N	F,G, J		
itan	36pF (360)	N	N	N		F,G, J		
Capacitance	39pF (390)	N	N	N		F,G, J		
ပိ	43pF (430)	N	N	N		F,G, J		
	47pF (470)	N	N	N		F,G, J		
	56pF (560)	N	N	N		F,G, J		
	68pF (680)	N	N			F,G, J		
	82pF (820)	N	N			F,G, J		
	100pF (101)	N	N			F,G, J		

^{1.} The letter in cell is expressed the symbol of product thickness.

Electrical Characteristics

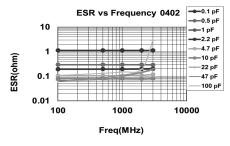


Fig. 3 ESR vs. Frequency (0402 size)

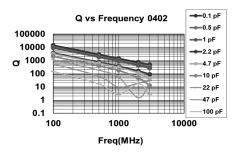


Fig. 5 Q vs. Frequency (0402 size)

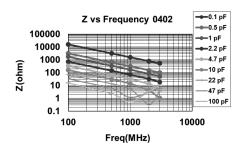


Fig. 7 Impedance vs. Frequency (0402 size)





Reliability Test Conditions And Requirements

No	Item	Test Condition	Requirements
1	Visual and Mechanical	-	No remarkable defect. Dimensions to conform to individual specification sheet.
2	Capacitance	* 1.0±0.2Vrms, 1MHz±10%	* Shall not exceed the limits given in the detailed
3	Q/ D.F. (Dissipation Factor)	* Test temp.: Room Temperature.	spec. * 01005, 0201, 0402/25V~50V: Cap<30pF,Q≥400+20C;Cap≥30pF, Q≥1000 *0402/100V~200V, 0603, 0805, 0505, 1111: Cap<30pF:Q≥800+20C;Cap≥30pF:Q≥1400
4	Dielectric Strength	*To apply voltage: ≤100V: 250% of rated voltage.(RF02: 300% of rated voltage.) 200V ~ 300V: 200% of rated voltage. 500V ~ 999V: 150% of rated voltage. 1000V ~ 3000V: 120% of rated voltage. 4000V: 110% of rated voltage. *Duration: 1 to 5 sec. *Charge & discharge current less than 50mA.	* No evidence of damage or flash over during test.
5	Insulation Resistance	* Test temp.: Room Temperature. ≤100V : To apply rated voltage for max. 120 sec. ≥200V :To apply rated voltage (500V max.) for 60 sec.	≥10GΩ or RxC≥100Ω-F whichever is smaller
6	Temperature Coefficient	* With no electrical load. * Operating temperature: NP0: -55~125°C at 25°C	* Capacitance change: within ±30ppm/°C;
7	Adhesive Strength of Termination	* Pressurizing force: 01005: 1N * Test time: 10±1 sec.	* No remarkable damage or removal of the terminations.
8	Vibration Resistance	* Vibration frequency: 10~55 Hz/min. * Total amplitude: 1.5mm * Test time: 6 hrs. (Two hrs each in three mutually perpendicular directions.) *Cap./DF(Q) Measurement to be made after de-aging at 150°C for 1hr then set for 24±2 hrs at room temp.	* No remarkable damage. * Cap change and Q/D.F.: To meet initial spec.
9	Solderability	* Solder temperature: 235±5°C * Dipping time: 2±0.5 sec.	95% min. coverage of all metalized area.
10	Bending Test	* The middle part of substrate shall be pressurized by means of the pressurizing rod at a rate of about 1 mm per second until the deflection becomes 1 mm and then the pressure shall be maintained for 5±1 sec. * Measurement to be made after keeping at room temp. for 24±2 hrs.	* No remarkable damage. * Cap change: within ±5.0% or ±0.5pF whichever is larger. (This capacitance change means the change of capacitance under specified flexure of substrate from the capacitance measured before the test.)
11	Resistance to Soldering Heat	* Solder temperature: 260±5°C * Dipping time: 10±1 sec * Preheating: 120 to 150°C for 1 minute before imme rse the capacitor in a eutectic solder. * Cap. / DF(Q) / I.R. Measurement to be made after de-aging at 150°C for 1hr then set for 24±2 hrs at room temp.	* No remarkable damage. * Cap change: within ±2.5% or ±0.25pF whichever is larger. * Q/D.F., I.R. and dielectric strength: To meet initial requirements. * 25% max. leaching on each edge.

^{* &}quot;Room condition" Temperature: 15 to 35°C, Relativ e humidity: 25 to 75%, Atmospheric pressure: 86 to 106kPa.





No	Item		Test Condition	on		Requirements
			ct the five cycles according to	the temp	peratures and	
		Step	Temp. (°C)	Time (min.)		
		1	Min. operating temp. +0/-3	30±3	i	* No remarkable damage.
	Temperature	2	Room temp.	2~3		* Cap change: within ±2.5% or ±0.25pF
12	Cycle	3	Max. operating temp. +3/-0	30±3		whichever is larger. * Q/D.F., I.R. and dielectric strength: To meet
		4	Room temp.	2~3		initial requirements.
		10°C fc	initial measurement (Class II or or 1 hr and then set for 24±2 h rement to be made after keepi rs.	rs at roo	m temp.	
	Humidity		emp.: 40±2°C			* No remarkable damage.
	(Damp Heat) Steady State	* Test ti	dity: 90~95% RH ime: 500+24/-0hrs. / DF(Q) / I.R. Measurement to	be mad	e after de-aging	* Cap change: within ±5.0% or ±0.5pF whichever is larger.
13.			0°C for 1hr then set for 24±2 h			* Q/D.F. value: Cap≥30pF, Q≥350; 10pF≤Cap<30pF, Q≥275+2.5C Cap<10pF; Q≥200+10C
						* I.R.: ≥1GΩ.
14	Humidity	* Test temp.: 40±2°C		* No remarkable damage.		
	(Damp Heat) Load	* Test	* Humidity: 90~95%RH * Test time: 500+24/-0 hrs. * To apply voltage: rated voltage (MAX. 500V) * Cap. / DF(Q) / I.R. Measurement to be made after de-aging at 150°C for 1hr then set for 24±2 hrs at		* Cap change: within ±7.5% or ±0.75pF whichever is larger.	
		* Cap.			made after	* Q/D.F. value: Cap≥30pF, Q≥200; Cap<30pF, Q≥100+10/3C
		room temp.			* I.R.: ≥500MΩ.	
15	High		temp.: NP0: 125±3°C			* No remarkable damage.
	Temperature Load	* To ap	X8G: 150±3°C * To apply voltage:		_	* Cap change: within ±3.0% or ±0.3pF whichever is larger.
	(Endurance)	(2) ≤6. (3) Ur≥	V≤Ur<500V: 200% of rated 3V or 500V: 150% of rated ≥630V: 120% of rated volta time: 1000+24/-0 hrs.	l voltag		* Q/D.F. value: Cap≥30pF, Q≥350 10pF≤Cap<30pF, Q≥275+2.5C Cap<10pF, Q≥200+10C
		* Cap. / DF(Q) / I.R. Measurement to be made after de-aging at 150°C for 1hr then set for 24±2 hrs at room temp		* I.R.: ≥1GΩ.		
16	ESR		SR should be measured at	room t	emperature	0.2pF≤Cap≤1pF:< 700mΩ/pF
		and tested at frequency 1±0.1 GHz.		1pF <cap≤2pf:< 600mω<="" td=""></cap≤2pf:<>		
		acireq	at frequency I±0.1 GHZ.		2pF <cap≤5pf:< 500mω<="" td=""></cap≤5pf:<>	
					5pF <cap≤10pf:< 300mω<="" td=""></cap≤10pf:<>	
						10pF <cap≤22pf:< 350mω<="" td=""></cap≤22pf:<>
		and te		room t	emperature	0201, 22pF≤Cap≤33pF: < 300mΩ 1111, 100pF <cap≤1000pf: 150mω<="" <="" td=""></cap≤1000pf:>
			uency 500±50 MHz.			1111, 100pt Cap=1000pr. > 130fft

^{* &}quot;Room condition" Temperature: 15 to 35°C, Relativ e humidity: 25 to 75%, Atmospheric pressure: 86 to 106kPa.





Tape & Reel Dimensions

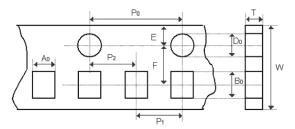


Fig. 21 The dimension of paper tape

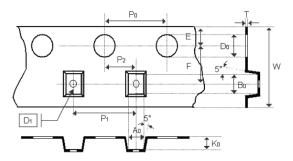


Fig. 22 The dimension of plastic tape

Size	0402
Chip Thickness	N
A ₀	0.7 +/-0.2
B ₀	1.2 +/-0.2
Т	≤0.8
K ₀	
W	8 +/-0.3
P ₀	4 +/-0.1
10xP ₀	40 +/-0.1
P ₁	2 +/-0.05
P ₂	2 +/-0.05
D ₀	1.5 +0.1/-0
D ₁	
E	1.75 +/-0.1
F	3.5 +/-0.05

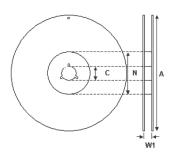


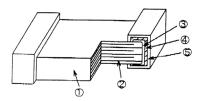
Fig. 23 The dimension of reel

Size	0402			
Reel size	7"	13"		
С	13 ±0.5			
W ₁	10 ±1.5			
Α	178 ±2	330 ±2		
N	60 +1/-0	50 min		



Appendixes

No.	Na	me	NP0
1	Ceramic	material	Hi-Q dielectric ceramic
2	Inner el	ectrode	Cu
3		Inner layer	Cu
4	Termination	Middle layer	Ni
5		Outer layer	Sn (Matt)



The construction of MLCC

Storage and handling conditions

- (1) To store products at 5 to 40°C ambient temperature and 20 to 70%. related humidity conditions; MSL Level 1.
- (2) The product is recommended to be used within one year after shipment. Check solderability in case of shelf life extension is needed.

Cautions:

- a. The corrosive gas reacts on the terminal electrodes of capacitors, and results in the poor solderability. Do not store the capacitors in the ambience of corrosive gas (e.g., hydrogen sulfide, sulfur dioxide, chlorine, ammonia
- b. In corrosive atmosphere, solderability might be degraded, and silver migration might occur to cause low reliability.
- c. Due to the dewing by rapid humidity change, or the photochemical change of the terminal electrode by direct sunlight, the solderability and electrical performance may deteriorate. Do not store capacitors under direct sunlight or dewing condition. To store products on the shelf and avoid exposure to moisture.

Recommended soldering conditions

The lead-free termination MLCCs are not only to be used on SMT against lead-free solder paste, but also suitable against lead-containing solder paste. If the optimized solder joint is requested, increasing soldering time, temperature and concentration of N2 within oven are recommended.

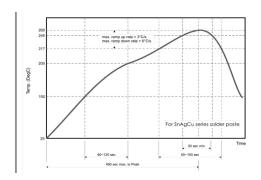


Fig. 25 Recommended reflow soldering profile for SMT process with SnAgCu series solder paste.

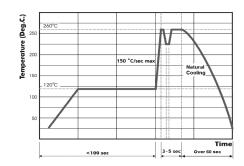


Fig. 26 Recommended wave soldering profile for SMT process with SnAgCu series solder.





Part Number Table

Description	Part Number
SMD Multilayer Ceramic Capacitors, 0402, NPO, 10pF, 1%, 50V	MCRF15N100F500CT
SMD Multilayer Ceramic Capacitors, 0402, NPO, 100pF, 1%, 25V	MCRF15N101F250CT
SMD Multilayer Ceramic Capacitors, 0402, NPO, 12pF, 1%, 50V	MCRF15N120F500CT
SMD Multilayer Ceramic Capacitors, 0402, NPO, 22pF, 1%, 50V	MCRF15N220F500CT

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